

# MOTOROLA SEMICONDUCTOR TECHNICAL DATA

## The RF Line NPN Silicon RF Power Transistors

Designed for 24 Volt UHF large-signal, common emitter, Class AB and Class A linear amplifier applications in industrial and commercial FM/AM equipment operating in the range 800–960 MHz.

- Specified 24 Volt,  $I_{CQ} = 8.0$  mA (Class AB), 900 MHz Characteristics  
Output Power = 3.0 Watts  
Minimum Gain = 10 dB @ 900 MHz  
Minimum Efficiency = 30% @ 900 MHz, 3.0 Watts  
Maximum Intermodulation Distortion –30 dBc @ 3.0 Watts (PEP)
- Characterized with Series Equivalent Large-Signal Parameters from 800 to 960 MHz
- Silicon Nitride Passivated
- 100% Tested for Load Mismatch Stress at all Phase Angles with 5:1 VSWR @ 26 Vdc, at rated output power
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

### MRF896

Motorola Preferred Device

3.0 W, 900 MHz  
RF POWER  
TRANSISTORS  
NPN SILICON



CASE 305-01, STYLE 1  
MRF896

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	30	Vdc
Collector-Emitter Voltage	$V_{CES}$	55	Vdc
Emitter-Base Voltage	$V_{EBO}$	4.0	Vdc
Collector-Current — Continuous	$I_C$	0.45	Adc
Total Device Dissipation @ $T_C = 50^\circ\text{C}$ Derate Above $50^\circ\text{C}$	$P_D$	17 0.143	Watts W/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	–65 to +150	$^\circ\text{C}$

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	7.0	$^\circ\text{C/W}$

#### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise stated)

Characteristic	Symbol	Min	Typ	Max	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C = 20$ mA, $I_B = 0$ )	$V_{(BR)CEO}$	30	37	—	Vdc
Collector-Emitter Breakdown Voltage ( $I_C = 20$ mA, $V_{BE} = 0$ )	$V_{(BR)CES}$	55	92	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 1.0$ mA, $I_C = 0$ )	$V_{(BR)EBO}$	4.0	5.0	—	Vdc
Collector Cutoff Current ( $V_{CE} = 30$ Vdc, $V_{BE} = 0$ )	$I_{CES}$	—	1.0 nA	1.0	mA

#### ON CHARACTERISTICS

DC Current Gain ( $I_E = 100$ mA, $V_{CE} = 5.0$ Vdc)	$h_{FE}$	30	60	120	—
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Preferred devices are Motorola recommended choices for future use and best overall value.

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MRF896  
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MOTOROLA RF DEVICE DATA